



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

ES1A THRU ES1J 1.0 AMP SURFACE MOUNT SUPER FAST RECTIFIERS



FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Super fast recovery time for high speed switching

MECHANICAL DATA

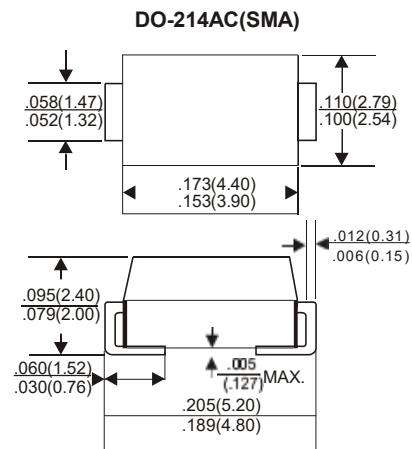
- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.063 gram

VOLTAGE RANGE

50 to 400 Volts

CURRENT

1.0 Ampere



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25 °C ambient temperature unless otherwise specified.

Single phase half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

TYPE NUMBER	ES1A	ES1B	ES1C	ES1D	ES1E	ES1G	ES1J	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	150	200	300	400	600	V
Maximum RMS Voltage	35	70	105	140	210	280	420	V
Maximum DC Blocking Voltage	50	100	150	200	300	400	600	V
Maximum Average Forward Rectified Current at T _L =110 C	1.0							A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	30							A
Maximum Instantaneous Forward Voltage at 1.0A	0.95		1.25		1.7		V	
Maximum DC Reverse Current at Rated DC Blocking Voltage	5.0							μA
Maximum Reverse Recovery Time (Note 1)	35							nS
Typical Junction Capacitance (Note 2)	10							pF
Operating and Storage Temperature Range T _J , T _{STG}	-65—+150							°C

NOTES:

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

RATING AND CHARACTERISTIC CURVES (ES1A THRU ES1J)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

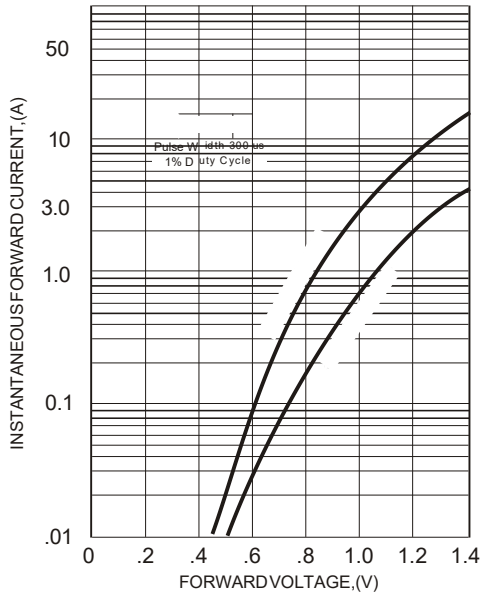


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

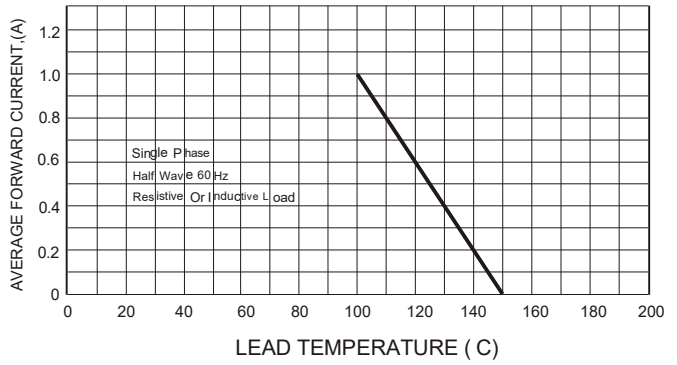
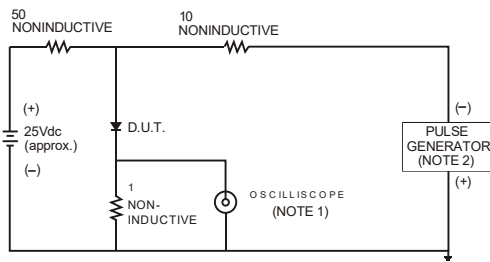


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm, 22pF.
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

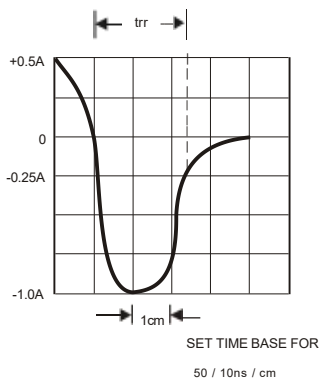


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

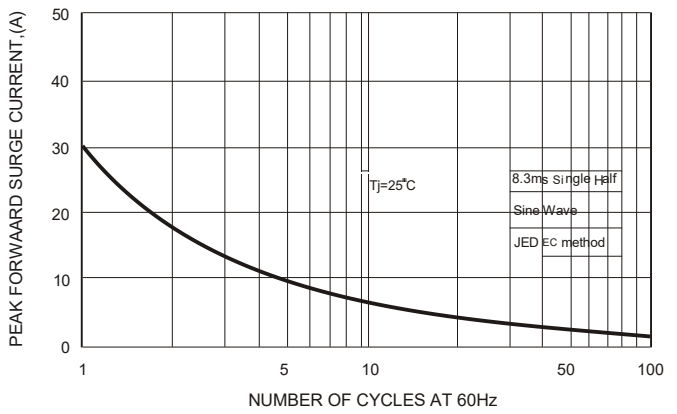


FIG.5-TYPICAL JUNCTION CAPACITANCE

